

	Hits	Search Text	DBs
1	270	(silane sih4 ("SiH.sub.4")) with ("nitrous oxide" n2o("N.sub.2O")) with (nitrogen n2 ("N.sub.2")) with (NH3 ("NH.sub.3"))	US-PGPUB; USPAT; USOCR
2	142	S62 and S79	US-PGPUB; USPAT; USOCR
3	7	("20010044220"   "4543707"   "5880018"   "6060132"   "6153541"   "6221794"   "6294460").PN. OR ("6410461").URPN.	US-PGPUB; USPAT; USOCR
4	1	("2001/0044220").URPN.	USPAT
5	71	S74 and "240" and degrees	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	1	S74 and "240" adj degrees	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	27748	Sion (silicon adj oxynitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	1378	S65 same S68	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
9	1771	(microelectromechanical or micro-electromechanical or micro-electro-mechanical or mems or microactuator) and magnet and coil	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	0	("2005/0088261").URPN.	USPAT
11	1	(microelectromechanical or micro-electromechanical or micro-electro-mechanical or mems or microactuator) and S70	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	230	S69 with S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13	1	S70 and cantilever	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
14	14288	silicon adj oxynitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	4544	S62 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	381	S63 same S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	5471	S68 with dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	17636	pecvd ("plasma enhanced chemical vapor deposition")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	1282	S63 and S65	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	264	(335/78.ccls. 200/181.ccls.) and (microelectromechanical or micro-electromechanical or micro-electro-mechanical or mems or microactuator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
21	129	S63 and (microelectromechanical or micro-electromechanical or micro-electro-mechanical or mems or microactuator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	2	("6768403").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
23	119	(335/78.ccls. 200/181.ccls.) and (microelectromechanical or micro-electromechanical or micro-electro-mechanical or mems or microactuator) and cantilever and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
24	60	(335/78.ccls. 200/181.ccls.) and (microelectromechanical or micro- electromechanical or micro-electro- mechanical or mems or microactuator) and substrate and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
25	169	(335/78.ccls. 200/181.ccls.) and (microelectromechanical or micro- electromechanical or micro-electro- mechanical or mems or microactuator) and dielectric and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
26	138005	dielectric same (silicon oxygen nitrogen si o n)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
27	96276	dielectric with (silicon oxygen nitrogen si o n)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
28	105	(335/78.ccls. 200/181.ccls.) and (microelectromechanical or micro- electromechanical or micro-electro- mechanical or mems or microactuator) and magnet\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
29	174	(335/78.ccls. 200/181.ccls.) and (microelectromechanical or micro- electromechanical or micro-electro- mechanical or mems or microactuator) and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
30	935	335/78.ccls. 200/181.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
31	26	333/101.ccls. and (microelectromechanical or micro- electromechanical or micro-electro- mechanical or mems or microactuator)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB